



FMMT634Q

#### 100V NPN DARLINGTON TRANSISTOR IN SOT23

### **Description**

This Bipolar Junction Transistor (BJT) has been designed to meet the stringent requirements of Automotive Applications.

#### **Features**

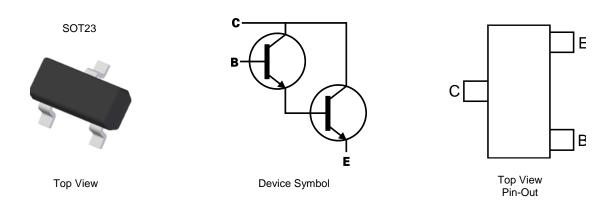
- BV<sub>CFO</sub> > 100V
- I<sub>C</sub> = 900mA High Continuous Collector Current
- I<sub>CM</sub> = 5A Peak Pulse Current
- 625mW Power Dissipation
- h<sub>FE</sub> > 5k up to 2A for High Current Gain Hold up
- Complementary PNP Type: FMMT734Q
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The FMMT634Q is suitable for automotive applications requiring specific change control; it is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.
- https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208@3
- Weight 0.008 grams (Approximate)

### **Applications**

- Automotive
- Lamp
- Relay
- Solenoid Driving



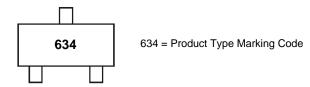
#### Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
FMMT634QTA	Automotive	634	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**





### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	120	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	$V_{EBO}$	12	V
Continuous Collector Current	Ic	900	mA
Peak Pulse Current	Ісм	5	Α

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	625	mW
Power Dissipation (Note 6)	P <sub>D</sub>	806	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	155	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R <sub>θJL</sub>	194	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	2
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

Notes:

- 5. For a device mounted with the exposed collector pad on 25mm × 25mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

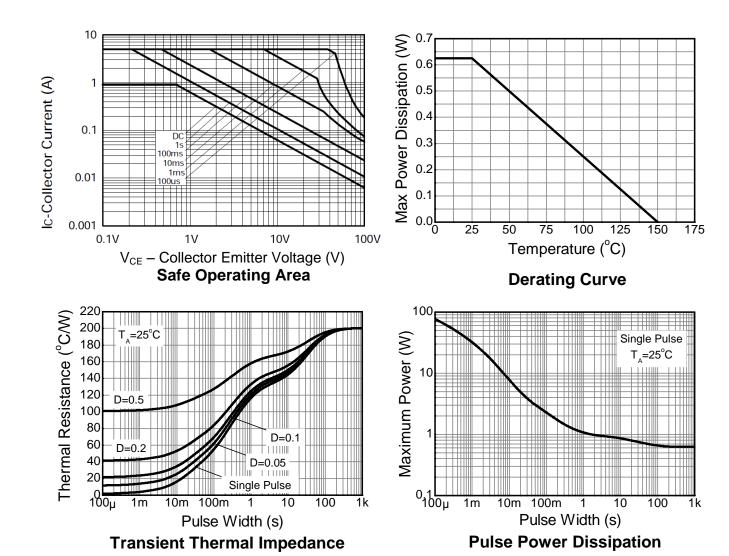
  6. Same as note (5), except the device is measured at t ≤ 5s.

  7. Thermal resistance from junction to solder-point (at the end of the collector lead).

  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics and Derating information**





# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	120	170	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	100	115	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	12	16	_	V	I <sub>E</sub> = 100μA
Collector Cut-Off Current	I <sub>CBO</sub>	_	<1	10	nA	V <sub>CB</sub> = 80V
Emitter Cut-Off Current	I <sub>EBO</sub>	_	<1	10	nA	$V_{EB} = 7V$
Collector Emitter Cut-Off Current	I <sub>CES</sub>	_	<1	100	nA	V <sub>CES</sub> = 80V
Static Forward Current Transfer Ratio (Note 9)	h <sub>FE</sub>	— 20k 15k 5k —	50k 60k 40k 14k 24k 600	_ _ _ _	_	$\begin{split} & I_{C} = 10 \text{mA},  V_{CE} = 5 \text{V} \\ & I_{C} = 100 \text{mA},  V_{CE} = 5 \text{V} \\ & I_{C} = 14,  V_{CE} = 5 \text{V} \\ & I_{C} = 24,  V_{CE} = 5 \text{V} \\ & I_{C} = 14,  V_{CE} = 2 \text{V} \\ & I_{C} = 54,  V_{CE} = 5 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 9)	VCE(sat)	_ _ _ _ _	0.67 0.72 0.78 0.75 0.82 0.68 0.85	0.75 0.80 1 0.85 0.93 — 0.96	٧	I <sub>C</sub> = 100mA, I <sub>B</sub> = 1mA I <sub>C</sub> = 250mA, I <sub>B</sub> = 1mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 1mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 5mA I <sub>C</sub> = 900mA, I <sub>B</sub> = 5mA I <sub>C</sub> = 900mA, I <sub>B</sub> = 5mA, T <sub>J</sub> = +150°C I <sub>C</sub> = 1A, I <sub>B</sub> = 5mA
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	_	1.5	1.65	<b>V</b>	$I_C = 1A, I_B = 5mA$
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(on)}$	_	1.33	1.50	V	$I_C = 1A$ , $V_{CE} = 5V$
Transition Frequency	f⊤	_	140	_	MHz	$I_{C} = 50 \text{mA}, V_{CE} = 10 \text{V},$ f = 100MHz
Output Capacitance	C <sub>obo</sub>	_	9	20	pF	V <sub>CB</sub> = 10V, f = 1MHz
Turn-On Time	t <sub>(on)</sub>		290	_	ns	$V_{CC} = 20V, I_C = 500mA,$
Turn-Off Time	t <sub>(off)</sub>	_	2,400	_	ns	$I_{B1} = -I_{B2} = 1mA$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



0.3

0

1mA

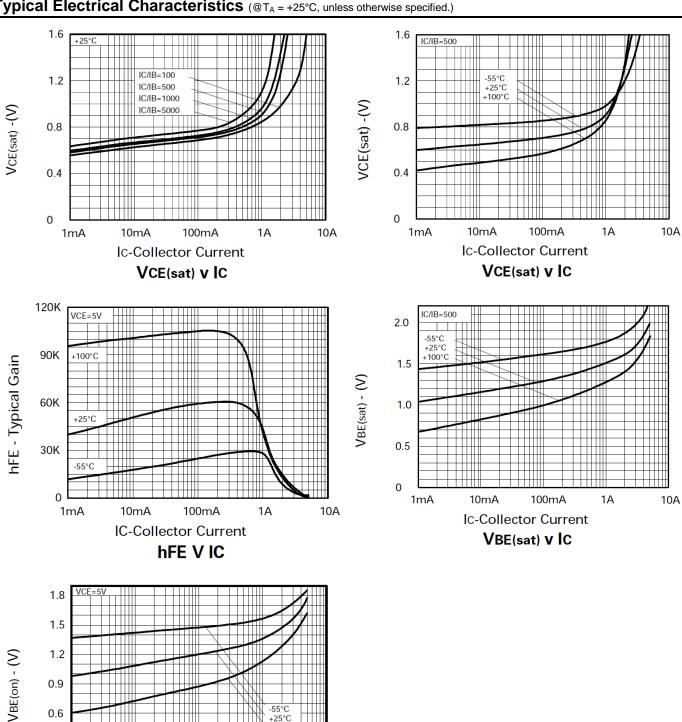
10mA

100mA

**Ic-Collector Current** VBE(on) v IC

1A

### Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)



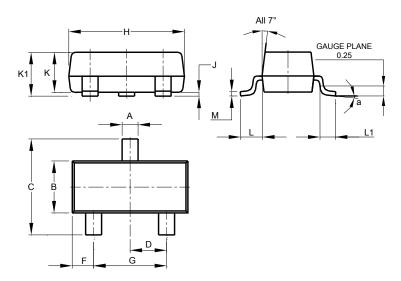
10A



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

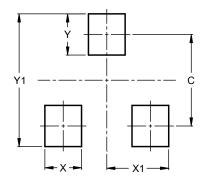


SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	0°	8°			
All Dimensions in mm					

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23



Dimensions	Value (in mm)			
С	2.0			
Х	0.8			
X1	1.35			
Y	0.9			
Y1	2.9			

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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